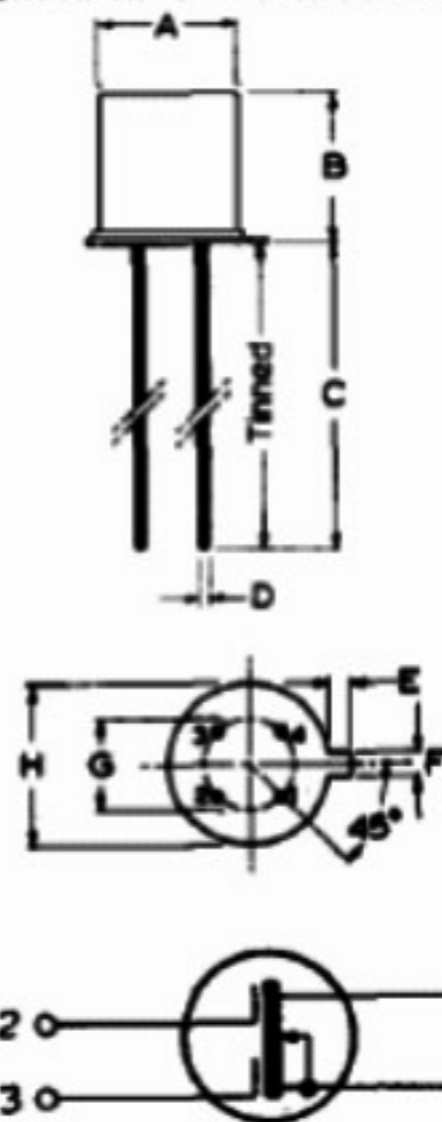


Conforms to J. E. D. E. C. TO-72



Millimetres

	Min.	Nom.	Max.
A	-	-	4.8
B	-	-	5.3
C	12.7	-	-
D	-	0.43	-
E	-	1.0	-
F	-	1.05	-
G	-	2.54	-
H	5.3	5.55	5.8

Connections

1. Drain
2. Gate 2
3. Gate 1
4. Source and substrate connected to case.

V_{DS} max.	Drain-source voltage	20	V
$+V_{G1S}$ max.	Gate 1-source voltage	8.0	V
$+V_{G2S}$ max.	Gate 2-source voltage	8.0	V
I_D max.	Drain current	20	mA
P_{tot} max.	Total device power dissipation ($T_{amb} \leq 25^\circ C$)	200	mW
T_j max.	Maximum junction temperature	135	$^\circ C$

Characteristics

$$I_D = 10\text{mA}, V_{DS} = 13\text{V}, V_{G2S} = +4.0\text{V}$$

$ y_{fs} $ typ.	Small signal forward transfer admittance in common source ($f = 1\text{kHz}$)	13	mmho
G_a typ.	Power gain ($f = 200\text{MHz}$)	18	dB
$-C_{rs}$ typ.	Feedback capacitance ($f = 10\text{MHz}$)	25	fF
N typ.	Noise figure at optimum source admittance ($f = 200\text{MHz}$)	3	dB